

TOSHIBA Transistor Silicon NPN Triple-Diffused Mesa Type

## 2SD2716

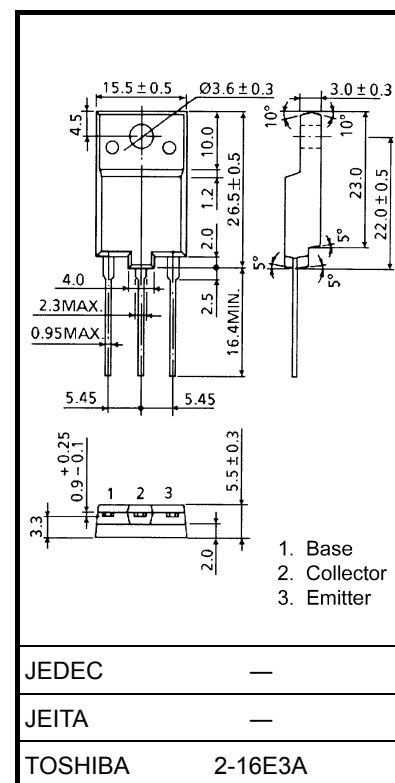
Horizontal Deflection Output for Color TVs

Unit: mm

- High voltage :  $V_{CBO} = 1500 \text{ V}$
- Low saturation voltage :  $V_{CE(sat)} = 5 \text{ V (max)}$
- High speed :  $t_f = 0.3 \mu\text{s (Typ.)}$
- Built-in damper type
- Collector metal (fin) is fully covered with mold resin.
- TO-3P(H)IS package

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristic		Symbol	Rating	Unit
Collector-base voltage		$V_{CBO}$	1500	V
Collector-emitter voltage		$V_{CEO}$	600	V
Emitter-base voltage		$V_{EBO}$	7	V
Collector current	DC	$I_C$	6	A
	Pulse	$I_{CP}$	12	
Base current		$I_B$	3	A
Collector power dissipation		$P_C$	50	W
Junction temperature		$T_j$	150	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	-55~150	$^\circ\text{C}$



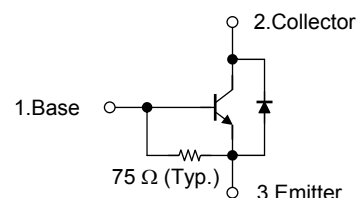
Weight: 5.5 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

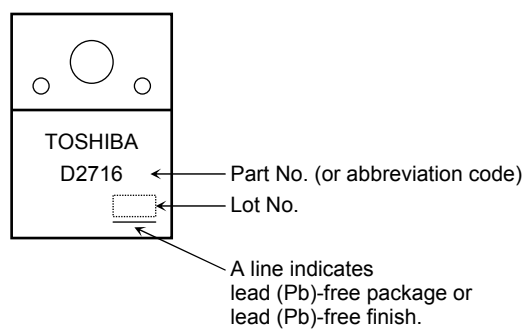
### Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal resistance, junction to case ( $T_c = 25^\circ\text{C}$ )	$R_{th(j-c)}$	2.5	$^\circ\text{C/W}$

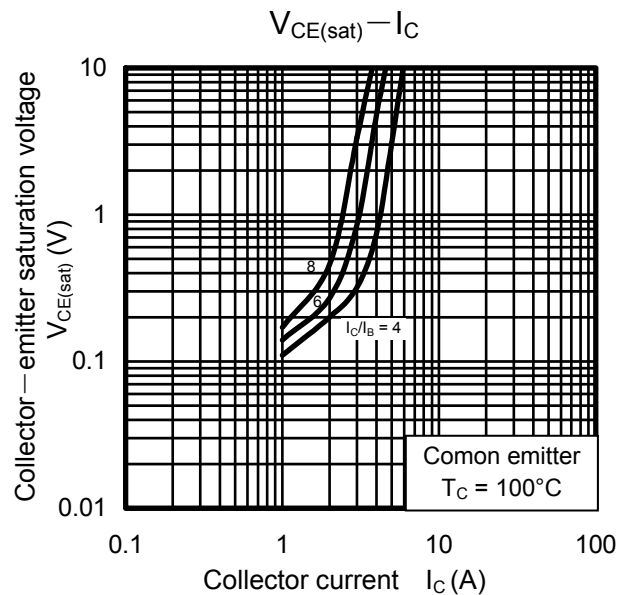
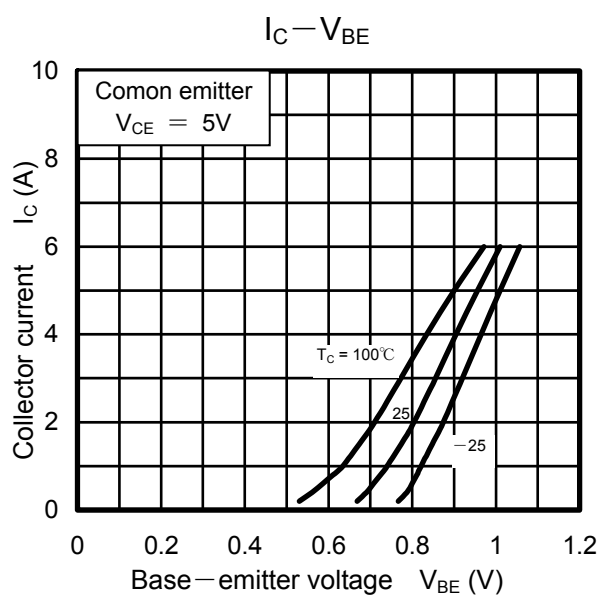
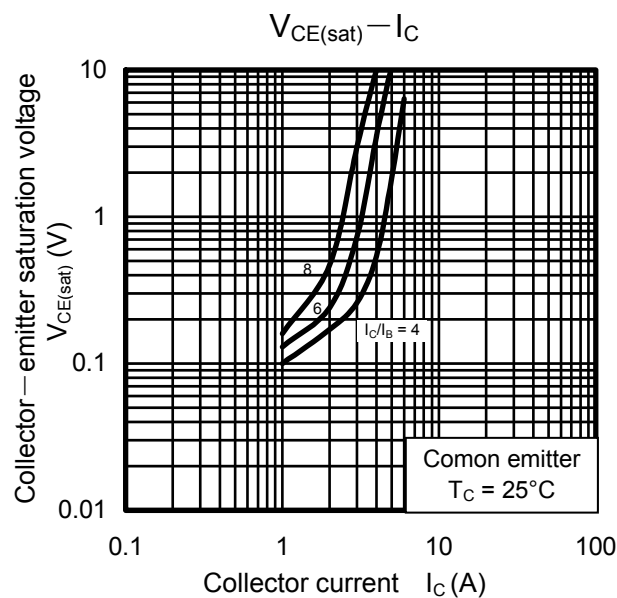
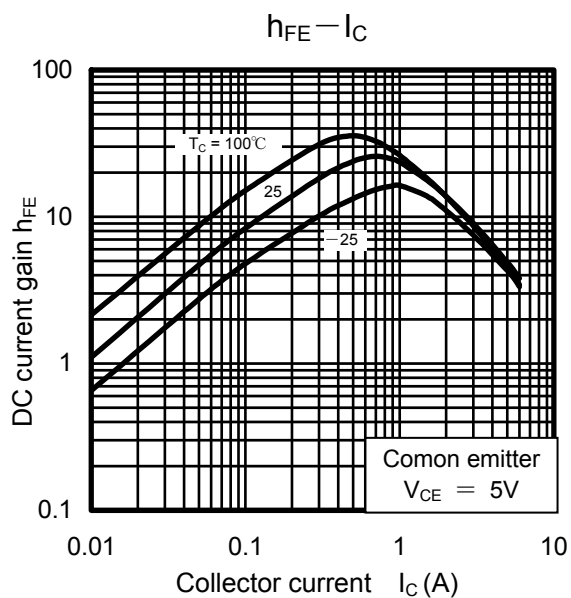
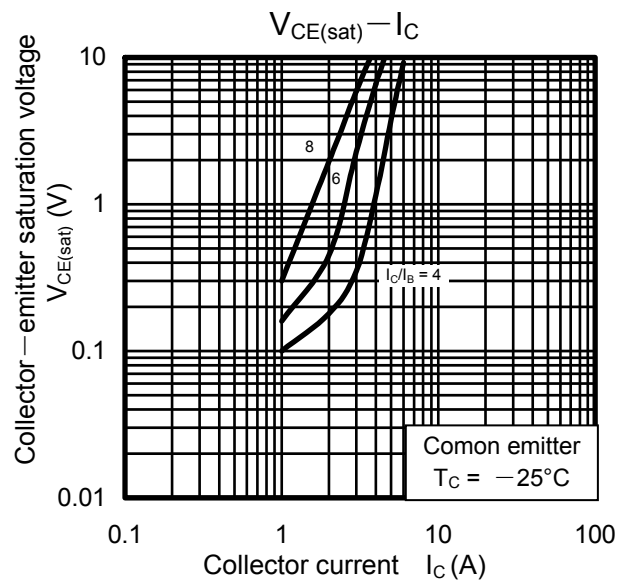
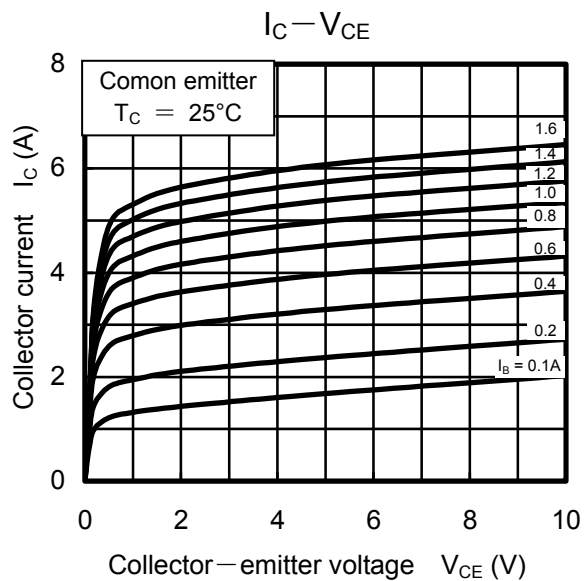
### Equivalent Circuit

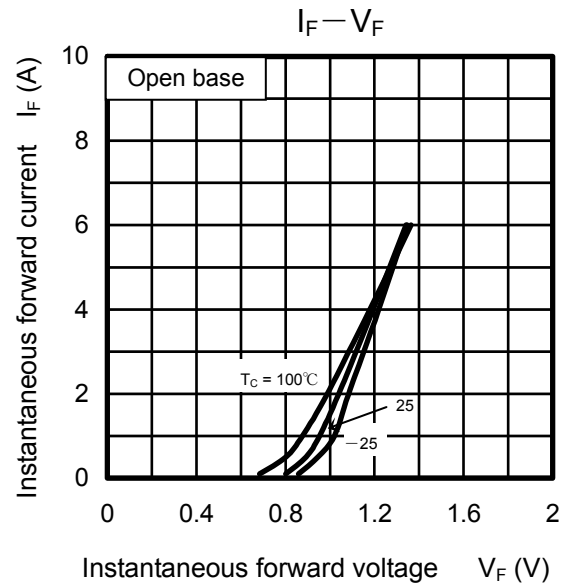
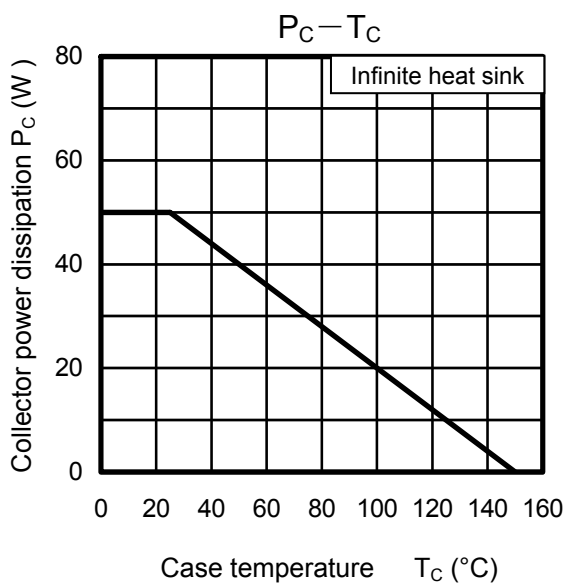
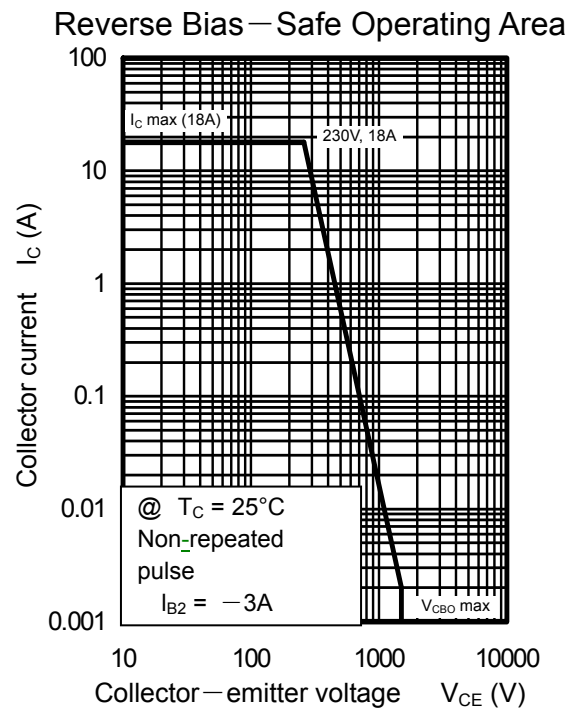
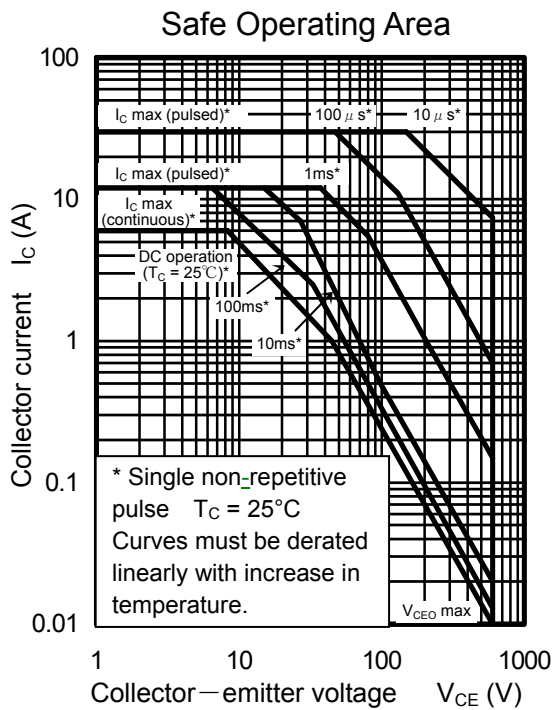
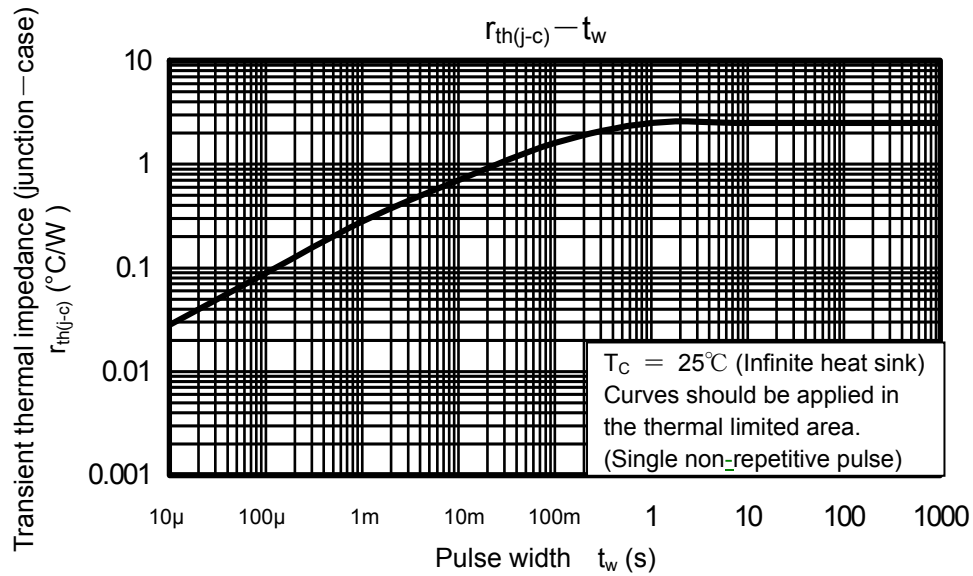


## Marking

Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 1500\text{ V}, I_E = 0$	—	—	1	mA
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 5\text{ V}, I_C = 0$	50	—	125	mA
Emitter-base breakdown voltage	$V_{(BR) EBO}$	$I_E = 400\text{ mA}, I_B = 0$	5	—	—	V
DC current gain	$h_{FE} (1)$	$V_{CE} = 5\text{ V}, I_C = 1\text{ A}$	15	—	33	—
	$h_{FE} (2)$	$V_{CE} = 5\text{ V}, I_C = 4\text{ A}$	5	—	8.2	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 4\text{ A}, I_B = 0.8\text{ A}$	—	—	5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 4\text{ A}, I_B = 0.8\text{ A}$	—	0.92	1.05	V
Forward voltage (damper diode)	$V_F$	$I_F = 6\text{ A}$	—	1.35	1.6	V
Transition frequency	$f_T$	$V_{CE} = 10\text{ V}, I_C = 0.1\text{ A}$	—	2	—	MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	63	—	pF
Switching time	Storage time	$I_{CP} = 4\text{ A}, I_{B1}(\text{end}) = 0.8\text{ A}$ $f_H = 15.75\text{ kHz}$	—	4.5	—	$\mu\text{s}$
	Fall time		—	0.3	—	





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